

IN THE CLAIMS

Per the revised amendment practice, a complete listing of all claims in the application follows.

Claims 1-59 (Canceled).

60. (Currently amended) A method of processing a substrate comprising two active areas and an intervening insulating region, said method comprising:

depositing an oxide charge barrier over said substrate;

depositing an ~~generally~~ insulative material over said oxide charge barrier, wherein

said ~~generally~~ insulative material is less insulative than said barrier; and

providing a ~~generally~~ conductive element over said ~~generally~~ insulative material,

wherein said element is generally laterally coextensive with said intervening insulating region.

61. (Currently amended) The method in claim 60, wherein said step of depositing an ~~generally~~ insulative material comprises depositing an ~~generally~~ insulative material that is allowed to comprise oxide charges.

62. (Previously presented) The method in claim 61, further comprising a step of plasma treating said substrate prior to said step of depositing an oxide charge barrier.

63. (Currently amended) The method in claim 61, further comprising:

annealing said ~~generally~~ insulative material;

allowing an oxide charge in said ~~generally~~ insulative material to migrate toward

said substrate in response to said annealing step; and

intercepting said oxide charge with said oxide charge barrier before said oxide

charge reaches said substrate.

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64. (Currently Amended) The method in claim 61, further comprising refraining from depositing any ~~generally~~ conductive material before said step of depositing an generally insulative material.
